

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Cancel claims 1-8.

9. (currently amended) Bipolar device, comprising:
- a collector region,
  - a base film disposed atop the collector region;
  - an emitter structure formed atop the base layer; and
  - a stress film disposed adjacent the emitter structure and atop the base film;
- wherein:
- the emitter structure is "T-shaped", having a lateral portion atop an upright portion;
  - a bottom of the upright portion forms a contact to the base film;
  - the lateral portion overhangs the base film;
  - the stress film comprises nitride; and
  - the stress film covers exposed surfaces of the emitter structure.

10. (Original) The bipolar device of claim 9, wherein the stress film is disposed in close proximity to an intrinsic portion of the device.

Cancel claim 11.

12. (Original) The bipolar device of claim 9, wherein the stress film is a compressive film.

13. (Original) The bipolar device of claim 9, wherein the stress film is a tensile film.

Cancel claim 14.

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15. (Original) The bipolar device of claim 9, wherein the stress film has at least 0.5GPa intrinsic stress.

16. (currently amended) ~~Bipolar device comprising:~~ The bipolar device of claim 9, wherein the stress film comprises:

means for creating compressive strain in the device to increase mobility of electrons in the device; and

means for creating tensile strain in the device to increase mobility of holes in the device.

17. (currently amended)) The bipolar device of claim 16, wherein the compressive and tensile strain are located in close proximity to an intrinsic portion of the device.

Cancel claims 18-20.